

Appl. No. 10/707,805
Amdt. dated January 6, 2005
Reply to Office action of October 06, 2004

Amendments to the Specification:

Please replace paragraph [0008] with the following amended paragraph:

[0008] However, for this prior-art method, when the photoresist layer 38 is used to define the shallow trench 42 for directly fabricating the STI 30, the photomask for defining the active area is susceptible to misalignmentso that the STI 30 shifts to one of the deep trenches 16, 18. As shown in Fig.4, the STI 30 leans toward the deep trench 16. In this situation, a serious defect may occur for the left trench capacitor 12. This is because the contact area of the storage node 24 and the buried strap 20 is reduced resulting in the resistance of the trench capacitor 12 being raised. Even more, the buried ~~[[trap]]~~ strap 20 may fail to contact the storage node 24 so as to cause a broken circuit. Consequently, the trench capacitor 12 cannot work.